

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

# 2SC2880

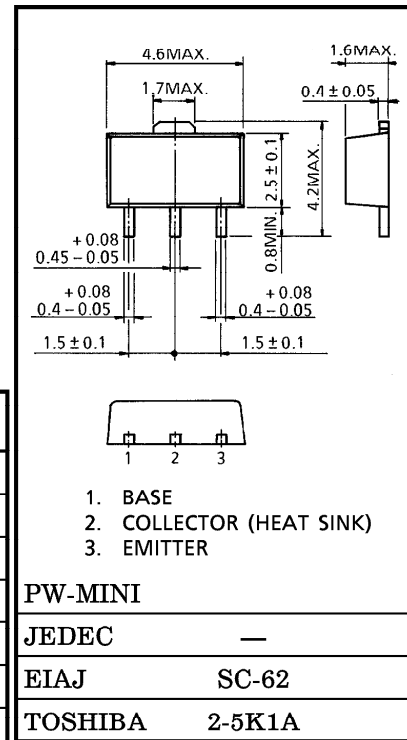
HIGH VOLTAGE SWITCHING APPLICATIONS.

Unit in mm

- High Voltage :  $V_{CEO} = 150V$
- High Transition Frequency :  $f_T = 120MHz$
- $P_C = 0.8 \sim 2W$  (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1200

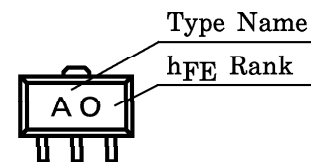
MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	200	V
Collector-Emitter Voltage	$V_{CEO}$	150	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	50	mA
Base Current	$I_B$	10	mA
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation	$P_C$ (Note)	800	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~150	$^\circ C$



Weight : 0.05g

Marking



Note : Mounted on ceramic substrate (250mm<sup>2</sup>×0.8t)

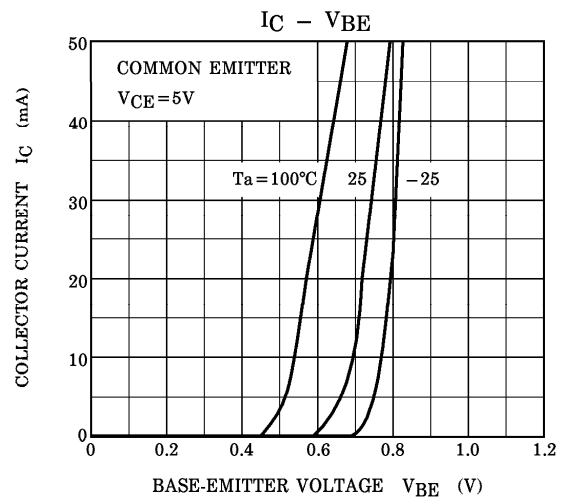
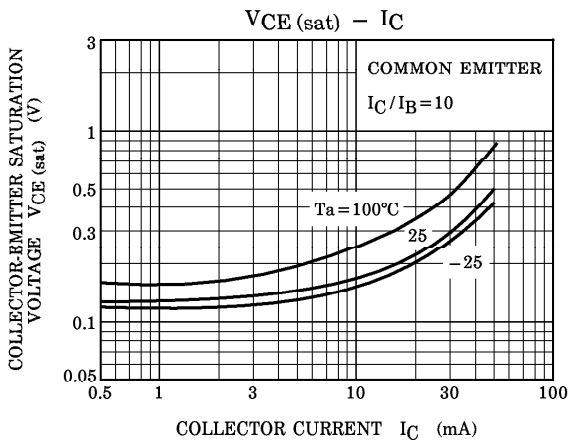
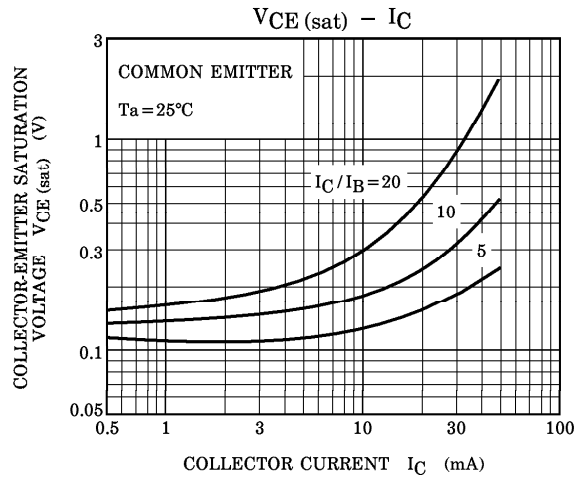
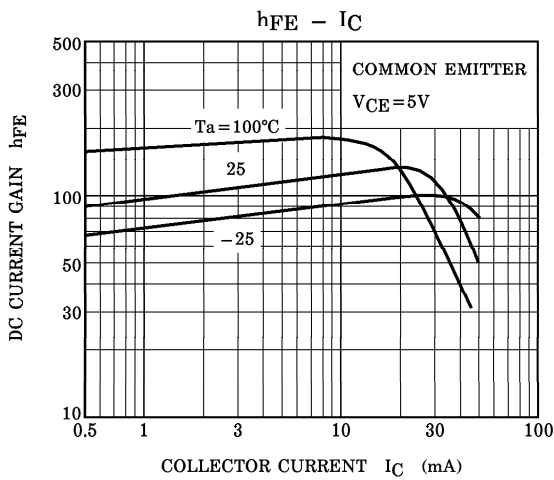
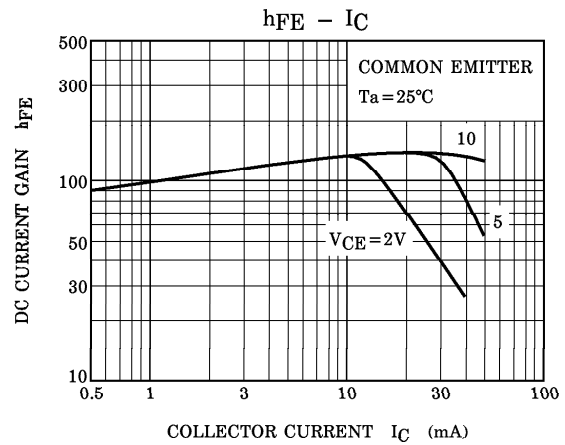
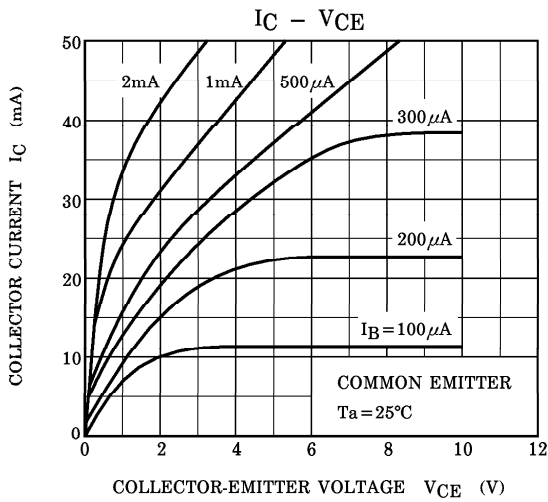
ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 200V, I_E = 0$	—	—	0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	—	—	0.1	$\mu A$
DC Current Gain	$h_{FE}$ (Note)	$V_{CE} = 5V, I_C = 10mA$	70	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$	—	—	0.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 5V, I_C = 30mA$	—	—	1	V
Transition Frequency	$f_T$	$V_{CE} = 30V, I_C = 10mA$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3.5	5.0	pF

Note :  $h_{FE}$  Classification O : 70~140, Y : 120~240

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